

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7MZ245FK

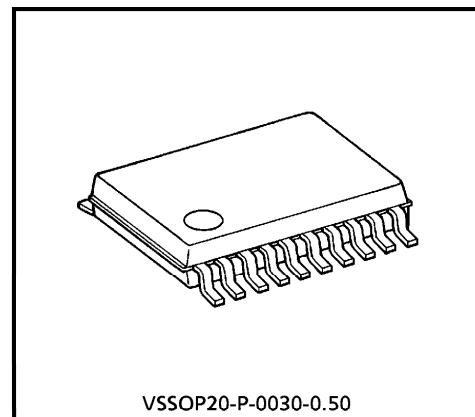
LOW VOLTAGE OCTAL BUS TRANSCEIVER WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC7MZ245 is a high performance CMOS OCTAL BUS TRANSCEIVER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3 V) V_{CC} applications, but it could be used to interface to 5 V supply environment for both inputs and outputs.

The direction of data transmission is determined by the level of the DIR input. The enable input (\overline{OE}) can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.



VSSOP20-P-0030-0.50
Weight : 0.03 g (typ.)

Features

- Low voltage operation : $V_{CC} = 2.0 \sim 3.6 \text{ V}$
- High speed operation : $t_{pd} = 7.0 \text{ ns (max)}$
($V_{CC} = 3.0 \sim 3.6 \text{ V}$)
- Output current : $|I_{OH}| / I_{OL} = 24 \text{ mA (min)}$
($V_{CC} = 3.0 \text{ V}$)
- Latch-up performance : $\pm 500 \text{ mA}$
- Available in VSSOP (US20)
- Bidirectional interface between 5 V and 3.3 V signals.
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 245 type.

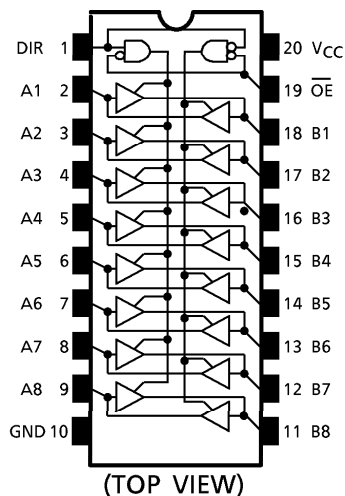
(Note) : Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

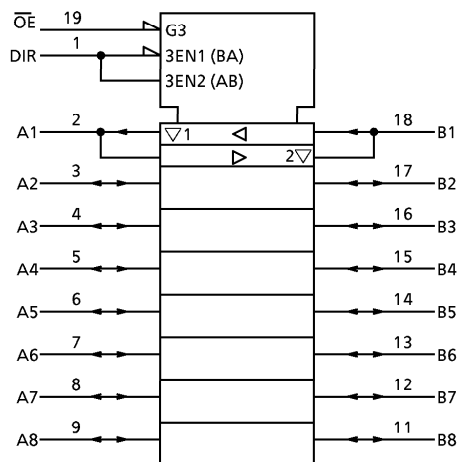
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Pin Assignment



IEC Logic Symbol



Truth Table

INPUTS		OUTPUTS	FUNCTION	
OE	DIR		A-BUS	B-BUS
L	L	A = B	OUTPUT	INPUT
L	H	B = A	INPUT	OUTPUT
H	X	Z	High Impedance	

X : Don't Care
 Z : High Impedance

Maximum Ratings

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7.0	V
DC Input Voltage (DIR, OE)	V _{IN}	-0.5~7.0	V
DC Bus I/O Voltage	V _{I/O}	-0.5~7.0 (Note 1)	V
		-0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	- 50	mA
Output Diode Current	I _{OK}	± 50 (Note 3)	mA
DC Output Current	I _{OUT}	± 50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} /Ground Current	I _{CC} /I _{GND}	± 100	mA
Storage Temperature	T _{stg}	- 65~150	°C

(Note 1) : Output in Off-State
 (Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.
 (Note 3) : V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Conditions

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage (DIR, \overline{OE})	V_{IN}	0~5.5	V
Bus I/O Voltage	$V_{I/O}$	0~5.5 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	± 24 (Note 7)	mA
		± 12 (Note 8)	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns/V

(Note 4) : Data Retention Only

(Note 5) : Output in Off-State

(Note 6) : High or Low State

(Note 7) : $V_{CC} = 3.0\sim 3.6$ V(Note 8) : $V_{CC} = 2.7\sim 3.0$ V(Note 9) : $V_{IN} = 0.8\sim 2.0$ V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC characteristics ($T_a = -40\sim 85^\circ\text{C}$)

PARAMETER		SYMBOL	TEST CONDITION	V_{CC} (V)	Min	Max	UNIT	
Input Voltage	"H" Level	V_{IH}		2.7~3.6	2.0	—	V	
	"L" Level	V_{IL}		2.7~3.6	—	0.8		
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	—	V
				$I_{OH} = -12 \text{ mA}$	2.7	2.2	—	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	—	
				$I_{OH} = -24 \text{ mA}$	3.0	2.2	—	
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	2.7~3.6	—	0.2	
				$I_{OL} = 12 \text{ mA}$	2.7	—	0.4	
				$I_{OL} = 16 \text{ mA}$	3.0	—	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	—	0.55	
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 5.5$ V		2.7~3.6	—	± 5.0	μA	
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\sim 5.5$ V		2.7~3.6	—	± 5.0	μA	
Power Off Leakage Current	I_{OFF}	$V_{IN}/V_{OUT} = 5.5$ V		0	—	10.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6	—	10.0	μA	
		$V_{IN}/V_{OUT} = 3.6\sim 5.5$ V		2.7~3.6	—	± 10.0		
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6$ V		2.7~3.6	—	500	μA	

AC Characteristic (Ta = -40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Min	Max	UNIT
Propagation Delay Time	t _{pLH}	(Fig.1, 2)	2.7	—	8.0	ns
	t _{pHL}		3.3 ± 0.3	1.5	7.0	
Output Enable Time	t _{pZL}	(Fig.1, 3)	2.7	—	9.5	ns
	t _{pZH}		3.3 ± 0.3	1.5	8.5	
Output Disable Time	t _{pLZ}	(Fig.1, 3)	2.7	—	8.5	ns
	t _{pHZ}		3.3 ± 0.3	1.5	7.5	
Output To Output Skew	t _{osLH}	(Note 10)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

(Note 10) : Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input t_r = t_f = 2.5 ns, C_L = 50 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Typ.	UNIT
Quiet Output Maximum Dynamic	V _{OLP}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V
Quiet Output Minimum Dynamic	V _{OLV}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Typ.	UNIT
Input Capacitance	C _{IN}	DIR, \overline{OE}	3.3	7	pF
Bus Input Capacitance	C _{I/O}	An, Bn	3.3	8	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10 MHz (Note 11)	3.3	25	pF

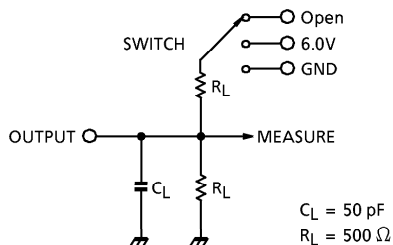
(Note 11) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

Test Circuit

Fig.1



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V
t_{pHZ}, t_{pZH}	GND

AC Waveform

Fig.2 t_{pLH}, t_{pHL}

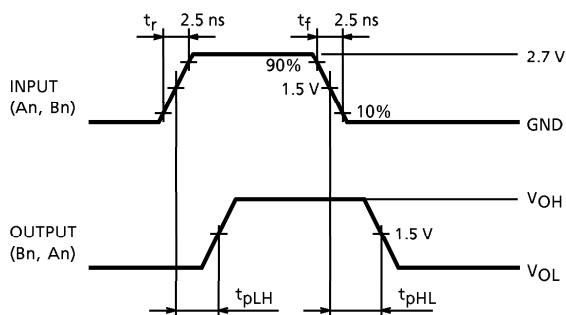
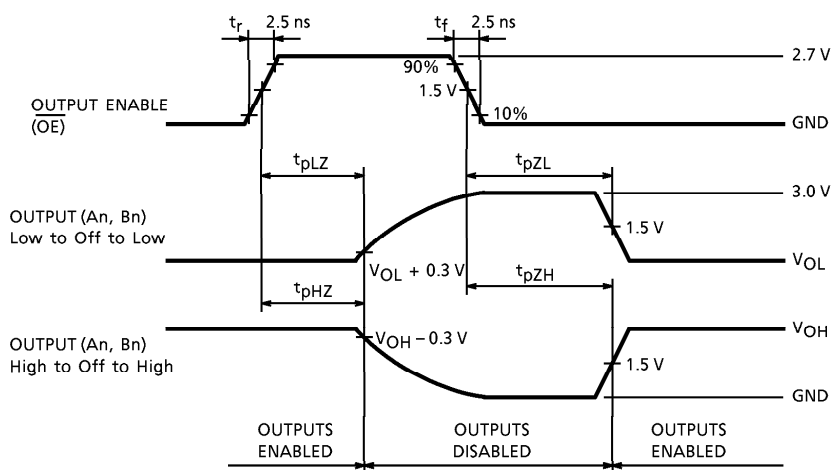
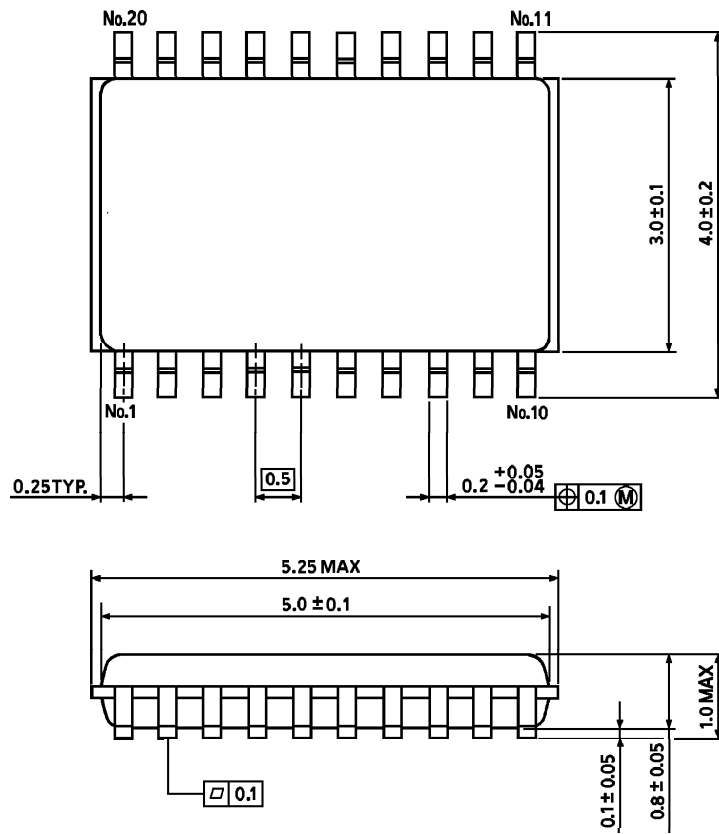


Fig.3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$



Outline Drawing
VSSOP20-P-0030-0.50

Unit : mm



Weight : 0.03 g (typ.)